BLC9G22LS-120VT

Power LDMOS transistor

AMPLEON

Rev. 2 — 5 July 2018

Product data sheet

1. Product profile

1.1 General description

120 W LDMOS power transistor with enhanced video bandwidth for base station applications at frequencies from 2110 MHz to 2180 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a common source class-AB production test circuit.

Test signal	f	I_{Dq}	V _{DS}	P _{L(AV)}	G _p	η _D	ACPR _{5M}
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2110 to 2180	700	28	30	18.1	31	-32.5 [<u>1</u>]

^[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF per carrier; 5 MHz carrier spacing.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable enhanced video bandwidth performance (75 MHz typical)
- Designed for broadband operation (2110 MHz to 2180 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 2110 MHz to 2180 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain	4 4 5	4.4.5
2	gate	4 1 5	1, 4, 5
3	source [1]		2
4	video decoupling	$\begin{bmatrix} 3 \\ 2 \end{bmatrix}$	3
5	video decoupling		aaa-003884
6	n.c.	6 2 7	
7	n.c.		

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage		
	Name	Description	Version	
BLC9G22LS-120VT	-	air cavity plastic earless flanged package; 6 leads	SOT1271-2	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-6	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _{case} = 80 °C; P _L = 30 W	0.47	K/W

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C per section, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.2 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 120 mA	1.5	1.9	3.1	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 700 mA	-	2.2	-	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	25	-	А
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	280	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 6 A	-	4.3	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 4.2 \text{ A}$	-	0.12	-	Ω

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; 3GPP test model 1 with 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF; f_1 = 2112.5 MHz; f_2 = 2117.5 MHz; f_3 = 2162.5 MHz; f_4 = 2167.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 700 mA; T_{case} = 25 °C; unless otherwise specified; in a water cooled class-AB test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 30 W	17.0	18.1	-	dB
η_{D}	drain efficiency	P _{L(AV)} = 30 W	28	31	-	%
RLin	input return loss	P _{L(AV)} = 30 W	-	-14	-9	dB
ACPR _{5M}	adjacent channel power ratio (5 MHz)	P _{L(AV)} = 30 W	-	-32.5	-29	dBc

Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; 3GPP test model 1 with 64 DPCH; PAR = 7.5 dB at 0.01 % probability on the CCDF; f = 2167.5 MHz; RF performance at $V_{DS} = 28$ V; $I_{Dq} = 700$ mA; $T_{case} = 25$ °C; unless otherwise specified; in a class-AB test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PARO	output peak-to-average ratio	P _{L(AV)} = 53 W	4	4.6	-	dB
$P_{L(M)}$	peak output power	P _{L(AV)} = 53 W	135	150	-	W

7. Test information

7.1 Ruggedness in class-AB operation

The BLC9G22LS-120VT is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 700 mA; P_{L} = 100 W (CW); f = 2110 MHz.

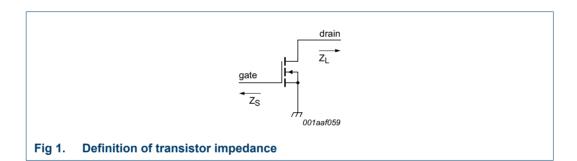
7.2 Impedance information

Table 9. Typical impedance

Measured load-pull data of the device; I_{Dq} = 700 mA; V_{DS} = 28 V; pulsed CW (t_p = 100 μ s; δ = 10 %).

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum pov	wer load				
2110	1.7 – j5.8	1.6 – j3.3	180.9	61.9	16.2
2140	2.0 – j6.2	1.7 – j3.2	179.0	62.7	16.4
2170	2.3 – j6.5	1.3 – j3.3	178.3	61.3	16.3
Maximum dra	in efficiency load				
2110	1.7 – j5.8	2.7 – j2.0	128.7	70.5	18.6
2140	2.0 – j6.2	2.7 – j2.0	127.0	70.0	18.6
2170	2.3 – j6.5	2.7 – j1.9	124.3	69.8	18.7

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.



7.3 Test circuit

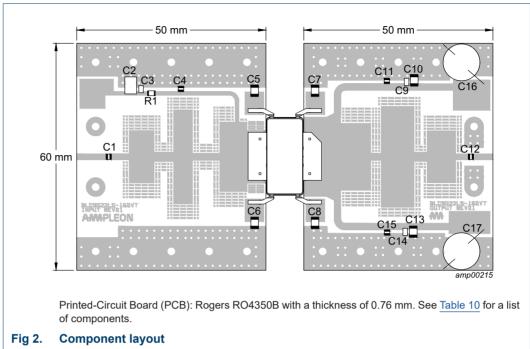
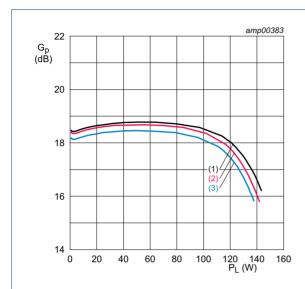


Table 10. List of components See Figure 2 for component layout.

Component	Description	Value	Remarks
C1, C4, C11, C12, C15	multilayer ceramic chip capacitor	33 pF	ATC 800B, vertical mounting
C2	multilayer ceramic chip capacitor	1 μF	Murata: GRM32RR71H105KA01L
C3	multilayer ceramic chip capacitor	100 nF	Murata: GRM21BR71H104KA01L
C5, C6, C7, C8, C10, C13	multilayer ceramic chip capacitor	4.7 μF, 50 V	Murata: GRM32ER71H475KA88L
C9, C14	multilayer ceramic chip capacitor	220 nF, 50 V	Murata: GRM21BR71H224KA01L
C16, C17	electrolytic capacitor	> 470 μF, 50 V	low ESR
R1	chip resistor	4.7 Ω, 1 %	SMD 0805

7.4 Graphical data

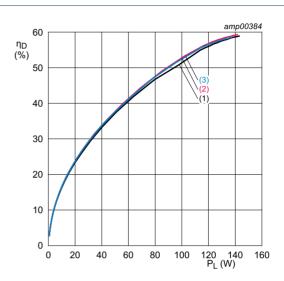
7.4.1 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 700 mA; t_p = 100 μ s; δ = 10 %.

- (1) f = 2115 MHz
- (2) f = 2145 MHz
- (3) f = 2175 MHz

Fig 3. Power gain as a function of output power; typical values

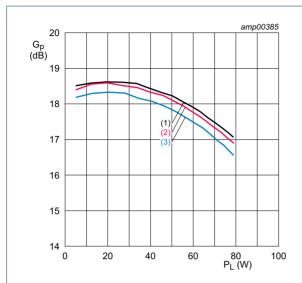


 V_{DS} = 28 V; I_{Dq} = 700 mA; t_p = 100 μs ; δ = 10 %.

- (1) f = 2115 MHz
- (2) f = 2145 MHz
- (3) f = 2175 MHz

Fig 4. Drain efficiency as a function of output power; typical values

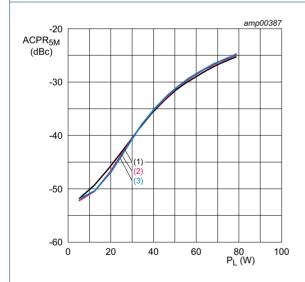
7.4.2 1-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 700 \text{ mA}.$

- (1) f = 2115 MHz
- (2) f = 2145 MHz
- (3) f = 2175 MHz

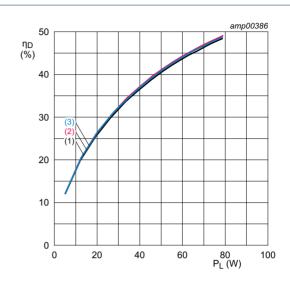
Fig 5. Power gain as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 700 \text{ mA}.$

- (1) f = 2115 MHz
- (2) f = 2145 MHz
- (3) f = 2175 MHz

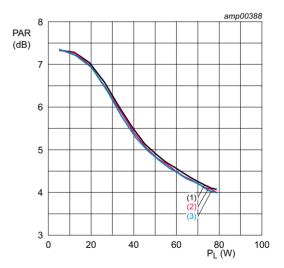
Fig 7. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 700 \text{ mA}.$

- (1) f = 2115 MHz
- (2) f = 2145 MHz
- (3) f = 2175 MHz

Fig 6. Drain efficiency as a function of output power; typical values

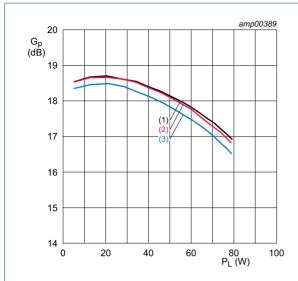


 $V_{DS} = 28 \text{ V}; I_{Dq} = 700 \text{ mA}.$

- (1) f = 2115 MHz
- (2) f = 2145 MHz
- (3) f = 2175 MHz

Fig 8. Peak-to-average power ratio as a function of output power; typical values

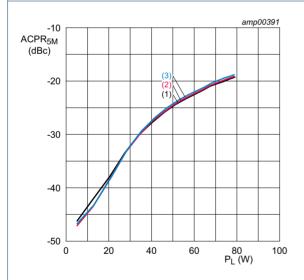
7.4.3 2-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 700 mA; 5 MHz spacing

- (1) f = 2115 MHz
- (2) f = 2145 MHz
- (3) f = 2175 MHz

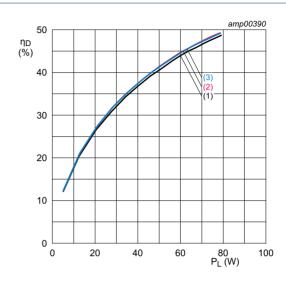
Fig 9. Power gain as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 700 mA; 5 MHz spacing

- (1) f = 2115 MHz
- (2) f = 2145 MHz
- (3) f = 2175 MHz

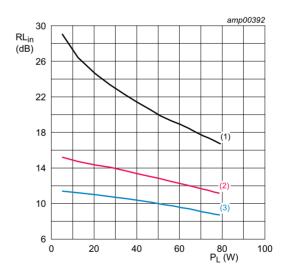
Fig 11. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 700 mA; 5 MHz spacing

- (1) f = 2115 MHz
- (2) f = 2145 MHz
- (3) f = 2175 MHz

Fig 10. Drain efficiency as a function of output power; typical values



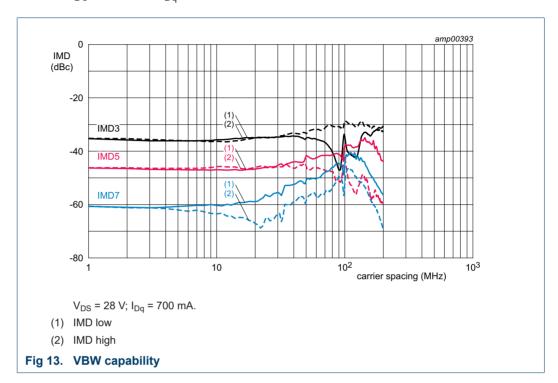
 V_{DS} = 28 V; I_{Dq} = 700 mA; 5 MHz spacing

- (1) f = 2115 MHz
- (2) f = 2145 MHz
- (3) f = 2175 MHz

Fig 12. Input return loss as a function of output power; typical values

7.4.4 2-Tone VBW

The BLC9G22LS-120VT shows 90 MHz (typical) video bandwidth (IMD third-order intermodulation inflection point) in a class-AB test circuit in the 2110 MHz to 2180 MHz band at V_{DS} = 28 V and I_{Dq} = 700 mA.



8. Package outline

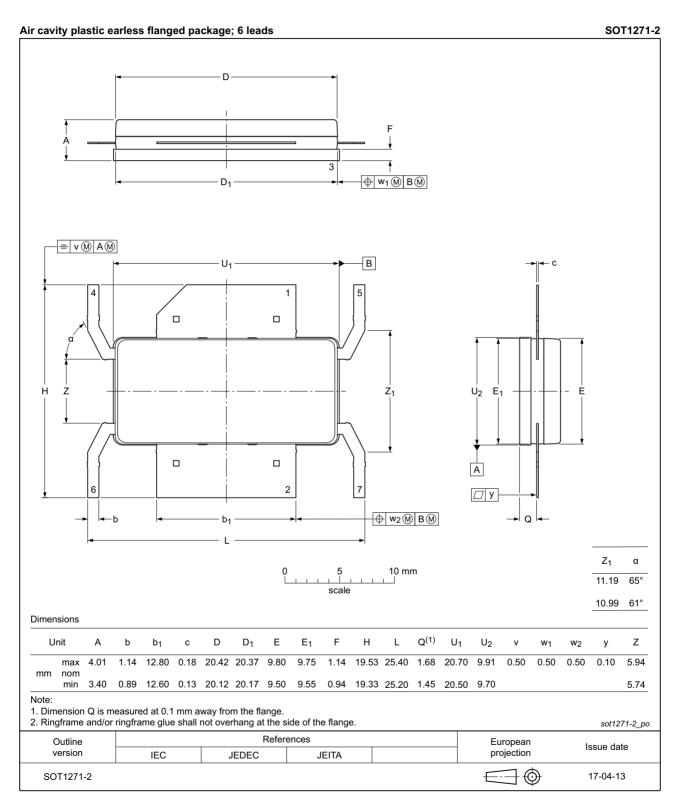


Fig 14. Package outline SOT1271-2

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

10. Abbreviations

Table 12. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
ESR	Equivalent Series Resistance
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9G22LS-120VT v.2	20180705	Product data sheet	-	BLC9G22LS-120VT v.1
Modifications	Section 1.2 on page 1: list item 5 updated			
BLC9G22LS-120VT v.1	20170714	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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Power LDMOS transistor

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Power LDMOS transistor

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